1 Block HV2 LDMOS Device
Number of fingers: 56, Periphery: 5.04 mm
Frequency: 1 GHz, V_{DS} =26 v & I_{DS} =2.0 mA/mm
50 ohm Termination
Solid:Simulated & Points:Measured

Output Power at Fundamental vs. Available Input Power
Single Tone Excitation

Transducer Gain vs. Available Input Power
Single Tone Excitation

Power Gain vs. Available Input Power
Single Tone Excitation

Drain Efficiency vs. Available Input Power
Single Tone Excitation
1 Block HV2 LDMOS Device
Number of fingers: 56, Periphery: 5.04 mm
Frequency: 1 GHz, $V_{DS}=26$ v & $I_{DS}=2.0$ mA/mm
50 ohm Termination
Solid: Simulated & Points: Measured

Drain Current vs. Available Input Power
Single Tone Excitation

Output Power at 2fo vs. Available Input Power
Single Tone Excitation

Output Power at 3fo vs. Available Input Power
Single Tone Excitation

Input Return Loss vs. Available Input Power
Single Tone Excitation
1 Block HV2 LDMOS Device
Number of fingers: 56, Periphery: 5.04 mm
Frequency: 1 GHz, $V_{DS} = 26 \, \text{v}$ & $I_{DS} = 2.0 \, \text{mA/mm}$
Tuned for Power
Solid: Simulated & Points: Measured

Output Power at Fundamental vs. Available Input Power
Single Tone Excitation

Transducer Gain vs. Available Input Power
Single Tone Excitation

Power Gain vs. Available Input Power
Single Tone Excitation

Drain Efficiency vs. Available Input Power
Single Tone Excitation
1 Block HV2 LDMOS Device
Number of fingers: 56, Periphery: 5.04 mm
Frequency: 1 GHz, $V_{DS} = 26$ v & $I_{DS} = 2.0$ mA/mm
Tuned for Power
Solid: Simulated & Points: Measured

**Drain Current vs. Available Input Power**
**Output Power at 2fo vs. Available Input Power**
**Output Power at 3fo vs. Available Input Power**
**Input Return Loss vs. Available Input Power**

**Single Tone Excitation**
1 Block HV2 LDMOS Device
Number of fingers: 56, Periphery: 5.04 mm
Frequency: 1 GHz, V_{DS} = 26 V & I_{DS} = 2.0 mA/mm
Tuned for Efficiency
Solid: Simulated & Points: Measured

Simulated: hv2emd09swp1.txt & Measured: hv2emd09.swp
Rev/Date: Rev0/0298
1 Block HV2 LDMOS Device
Number of fingers: 56, Periphery: 5.04 mm
Frequency: 1 GHz, $V_{DS} = 26$ v & $I_{DS} = 2.0$ mA/mm
Tuned for Efficiency
Solid: Simulated & Points: Measured

Drain Current vs. Available Input Power
Single Tone Excitation

Output Power at 2fo vs. Available Input Power
Single Tone Excitation

Output Power at 3fo vs. Available Input Power
Single Tone Excitation

Input Return Loss vs. Available Input Power
Single Tone Excitation

Simulated: hv2emd09swp1.txt & Measured: hv2emd09.swp
Rev/Date: Rev0/0298
1 Block HV2 LDMOS Device
Number of fingers: 56, Periphery: 5.04 mm
Frequency: 1 GHz, V_{DS} = 26 V & I_{DS} = 2.0 mA/mm
Tuned for Power & Efficiency
Solid: Simulated & Points: Measured

Output Power at Fundamental vs. Available Input Power
Single Tone Excitation

Transducer Gain vs. Available Input Power
Single Tone Excitation

Power Gain vs. Available Input Power
Single Tone Excitation

Drain Efficiency vs. Available Input Power
Single Tone Excitation
1 Block HV2 LDMOS Device
Number of fingers: 56, Periphery: 5.04 mm
Frequency: 1 GHz, $V_{DS} = 26\text{ v}$ & $I_{DS} = 2.0\text{ mA/mm}$
Tuned for Power & Efficiency
Solid: Simulated & Points: Measured

Drain Current vs. Available Input Power
Single Tone Excitation

Output Power at 2fo vs. Available Input Power
Single Tone Excitation

Output Power at 3fo vs. Available Input Power
Single Tone Excitation

Input Return Loss vs. Available Input Power
Single Tone Excitation

Simulated: hv2ped09swp1.txt & Measured: hv2ped09.swp
Rev/Date: Rev0/0298
1 Block HV2 LDMOS Device
Number of fingers: 56, Periphery: 5.04 mm
Frequency: 1 GHz, \(V_{DS} = 26\) V & \(I_{DS} = 2.0\) mA/mm
50 ohm Termination
Solid: Simulated & Points: Measured

Total Output Power vs. Available Input Power
Two Tone Excitation with 1 MHz Separation

Transducer Gain vs. Available Input Power
Two Tone Excitation with 1 MHz Separation

Power Gain vs. Available Input Power
Two Tone Excitation with 1 MHz Separation

PAE vs. Available Input Power
Two Tone Excitation with 1 MHz Separation

Rev/Date: Rev0/0298
Drain Current vs. Available Input Power
Two Tone Excitation with 1 MHz Separation

Drain Efficiency vs. Available Input Power
Two Tone Excitation with 1 MHz Separation

Output Power at Highest 3IMD vs. Available Input Power
Two Tone Excitation with 1 MHz Separation

Input Return Loss vs. Available Input Power
Two Tone Excitation with 1 MHz Separation

1 Block HV2 LDMOS Device
Number of fingers: 56, Periphery: 5.04 mm
Frequency: 1 GHz, $V_{DS} = 26\, \text{V}$ & $I_{DS} = 2.0\, \text{mA/mm}$

50 ohm Termination
Solid: Simulated & Points: Measured

Simulated: h2i50d09swp1.txt & Measured: h2i50d09.swp

Rev/Date: Rev0/0298
1 Block HV2 LDMOS Device
Number of fingers: 56, Periphery: 5.04 mm
Frequency: 1 GHz, $V_{DS} = 26\, \text{V}$ & $I_{DS} = 2.0\, \text{mA/mm}$
Tuned for Power
Solid: Simulated & Points: Measured

Total Output Power vs. Available Input Power
Two Tone Excitation with 1 MHz Separation

Transducer Gain vs. Available Input Power
Two Tone Excitation with 1 MHz Separation

Power Gain vs. Available Input Power
Two Tone Excitation with 1 MHz Separation

PAE vs. Available Input Power
Two Tone Excitation with 1 MHz Separation

Simulated: h2ipmd09swp1.txt & Measured: h2ipmd09.swp
Rev/Date: Rev0/0298
1 Block HV2 LDMOS Device
Number of fingers: 56, Periphery: 5.04 mm
Frequency: 1 GHz, \( V_{DS} = 26 \text{ v} \) & \( I_{DS} = 2.0 \text{ mA/mm} \)
Tuned for Power
Solid:Simulated & Points:Measured

Drain Current vs. Available Input Power
Two Tone Excitation with 1 MHz Separation

Drain Efficiency vs. Available Input Power
Two Tone Excitation with 1 MHz Separation

Output Power at Highest 3IMD vs. Available Input Power
Two Tone Excitation with 1 MHz Separation

Input Return Loss vs. Available Input Power
Two Tone Excitation with 1 MHz Separation
1 Block HV2 LDMOS Device  
Number of fingers: 56, Periphery: 5.04 mm  
Frequency: 1 GHz, $V_{DS} = 26$ V & $I_{DS} = 2.0$ mA/mm  
Tuned for Efficiency  
Solid: Simulated & Points: Measured

**Total Output Power vs. Available Input Power**  
Two Tone Excitation with 1 MHz Separation

**Transducer Gain vs. Available Input Power**  
Two Tone Excitation with 1 MHz Separation

**Power Gain vs. Available Input Power**  
Two Tone Excitation with 1 MHz Separation

**PAE vs. Available Input Power**  
Two Tone Excitation with 1 MHz Separation

Simulated: h2iemd09swp1.txt & Measured: h2iemd09.swp  
Rev/Date: Rev0/0298
1 Block HV2 LDMOS Device
Number of fingers: 56, Periphery: 5.04 mm
Frequency: 1 GHz, $V_{DS} = 26 \text{ V} \& I_{DS} = 2.0 \text{ mA/mm}$
Tuned for Efficiency
Solid:Simulated & Points:Measured

Drain Current vs. Available Input Power
Two Tone Excitation with 1 MHz Separation

Drain Efficiency vs. Available Input Power
Two Tone Excitation with 1 MHz Separation

Output Power at Highest 3IMD vs. Available Input Power
Two Tone Excitation with 1 MHz Separation

Input Return Loss vs. Available Input Power
Two Tone Excitation with 1 MHz Separation

Simulated:h2iemd09swp1.txt & Measured:h2iemd09.swp
Rev/Date: Rev0/0298
1 Block HV2 LDMOS Device
Number of fingers: 56, Periphery: 5.04 mm
Frequency: 1 GHz, $V_{DS} = 26$ v & $I_{DS} = 2.0$ mA/mm
Tuned for Power & Efficiency
Solid: Simulated & Points: Measured

Total Output Power vs. Available Input Power
Two Tone Excitation with 1 MHz Separation

Transducer Gain vs. Available Input Power
Two Tone Excitation with 1 MHz Separation

Power Gain vs. Available Input Power
Two Tone Excitation with 1 MHz Separation

PAE vs. Available Input Power
Two Tone Excitation with 1 MHz Separation

Simulated: h2iped09swp1.txt & Measured: h2iped09.swp
Rev/Date: Rev00298
1 Block HV2 LDMOS Device
Number of fingers: 56, Periphery: 5.04 mm
Frequency: 1 GHz, \(V_{DS}=26\) V & \(I_{DS}=2.0\) mA/mm
Tuned for Power & Efficiency
Solid: Simulated & Points: Measured

Drain Current vs. Available Input Power
Two Tone Excitation with 1 MHz Separation

Drain Efficiency vs. Available Input Power
Two Tone Excitation with 1 MHz Separation

Output Power at Highest 3IMD vs. Available Input Power
Two Tone Excitation with 1 MHz Separation

Input Return Loss vs. Available Input Power
Two Tone Excitation with 1 MHz Separation

Simulated: h2iped09swp1.txt & Measured: h2iped09.swp
Rev/Date: Rev0/0298
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